

Title (en)

Semiconductor wafer fabrication system having two energy detectors for a laser

Title (de)

System zur Herstellung eines Halbleiter-Wafers unter Verwendung von zwei Energiedetektoren für einen Laser

Title (fr)

Système de fabrication de plaquettes semiconductrices utilisant deux détecteurs d'énergie pour un laser

Publication

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Application

**EP 98938031 A 19980727**

Priority

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- US 90886297 A 19970808

Abstract (en)

[origin: WO9908133A2] A first laser light intensity detector is positioned within a stepper or scanner proximate to a reticle so that attenuation due to stepper optics has already occurred prior to the laser light impinging upon the light intensity detector. Preferably, the first light intensity detector is mounted as closed to the wafer as practical. A second light intensity detector is located at the output of the laser. The light intensity detected from the outputs of the first and second light intensity detectors, in conjunction, forms part of a feedback mechanism which adjusts the light output of the laser, during wafer fabrication, so that the light intensity detected by the first light intensity detector is an optimum value.

IPC 8 full level

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